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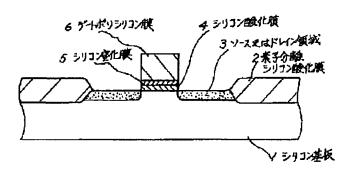
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TITLE

MOS TYPE FIELD EFFECT

TRANSISTOR AND ITS

MANUFACTURE



ABSTRACT: PURPOSE: To realize a surface channel type p+ polysilicon gate PMOS type field effect transistor which develops no punchthrough of baron and whose electric characteristics of device is the same as the case where a silicon oxide film is a gate insulating film.

> CONSTITUTION: A gate insulating film is of a double-layer structure of a silicon nitride film 5 and a silicon oxide film 4, and the silicon nitride film 5 is located on the gate electrode side.

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